### Vishay Siliconix



### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, b</sup>	t ≤ 10 s	R <sub>thJA</sub>	20	24	
Maximum Junction-to-Case (Drain Top) <sup>a</sup>	Steady State	R <sub>thJC</sub> (Drain)	1	1.2	°C/W
Maximum Junction-to-Case (Source) <sup>a, c</sup>	Sleady State	R <sub>thJC</sub> (Source)	2.8	3.4	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Maximum under Steady State conditions is 68 °C/W.

c. Measured at source pin (on the side of the package).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	40			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_J$	L 050 A		43.1		24/20	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA		- 6.9		mV/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1.5	2.2	3.0	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
	I <sub>DSS</sub>	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 V, V_{GS} = 10 V$	25			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 14 A		0.0046	0.0055	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12 A		0.0058	0.007		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 13.6 A		86		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			3800			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		510		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			160			
Tatal Cata Charge	Qg	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		51	77	nC	
Total Gate Charge				25	38		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 20$ V, $V_{GS} = 4.5$ V, $I_{D} = 20$ A		12			
Gate-Drain Charge	Q <sub>gd</sub>			7			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.1	1.7	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			45	70		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 2 $\Omega$		260	400		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega$ $\text{I}_{D} \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 4.5 \text{ V}, \text{ R}_{g} = 1 \Omega$		35	55		
Fall Time	t <sub>f</sub>			55	85		
Turn-On Delay Time	t <sub>d(on)</sub>			15	25	ns	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 2 $\Omega$		30	45		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		35	55		
Fall Time	t <sub>f</sub>			10	15		
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	۱ <sub>S</sub>	T <sub>C</sub> = 25 °C			50	А	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				80	~	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 10 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			85	130	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 10 A, dl/dt = 100 A/μs, T <sub>.1</sub> = 25 °C		110	170	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	$r_{\rm F} = 10$ A, u/ul = 100 A/µs, $r_{\rm J} = 25$ °C		64		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			21			

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %

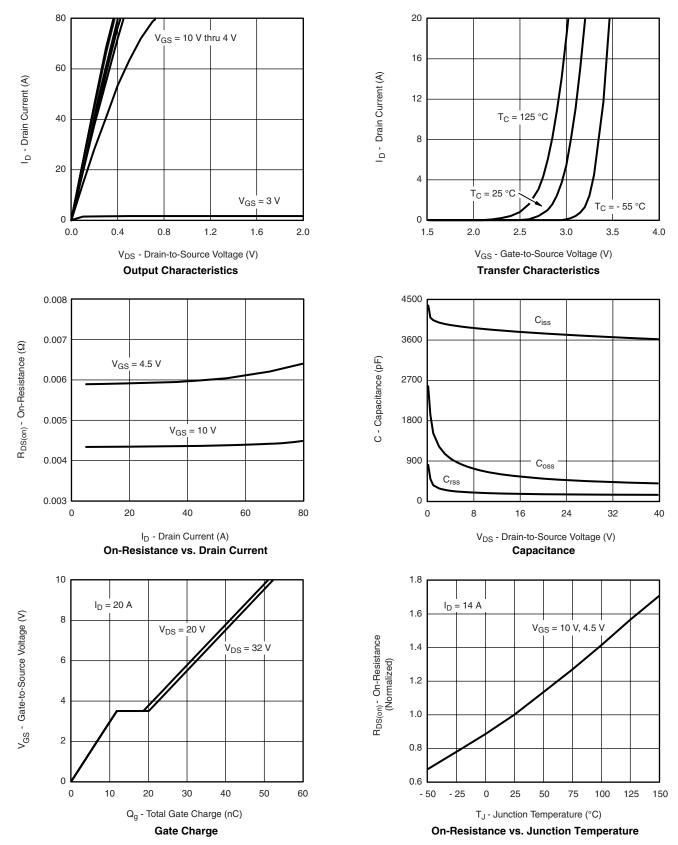
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## SiE832DF Vishay Siliconix

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



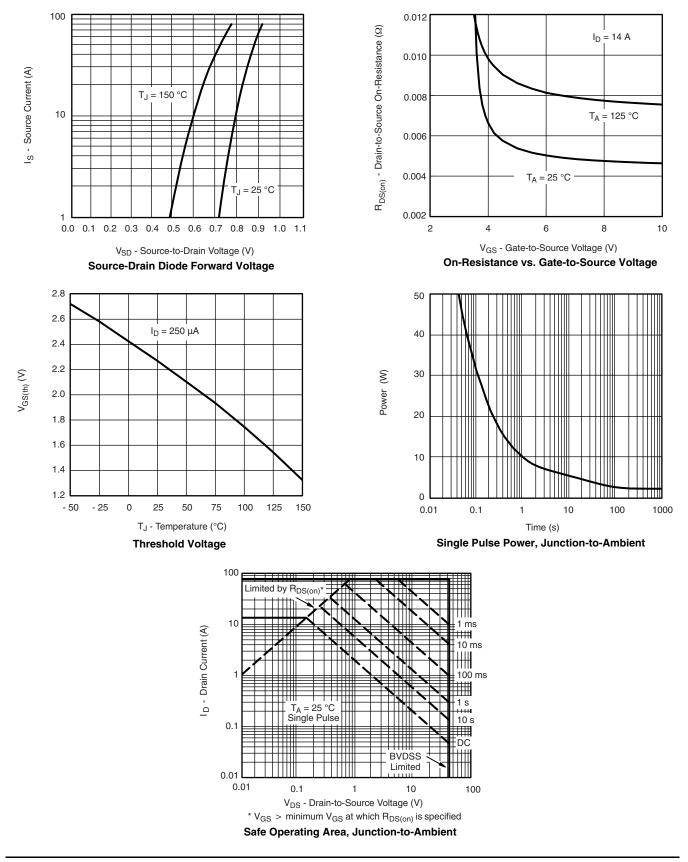
Document Number: 74414 S09-1338-Rev. C, 13-Jul-09

## SiE832DF

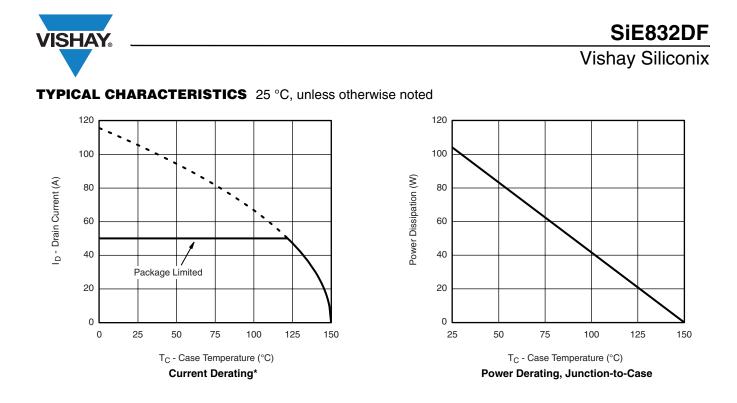




### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



4



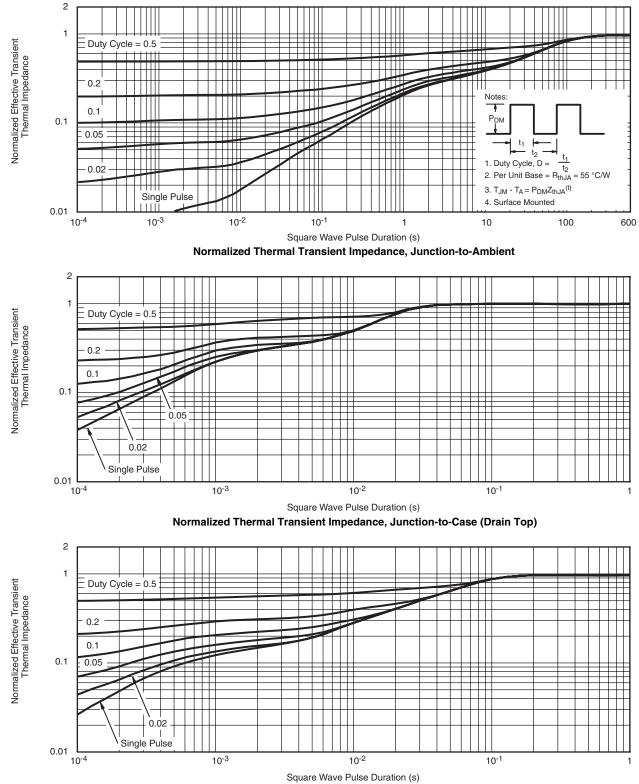
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## SiE832DF

### Vishay Siliconix



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Source

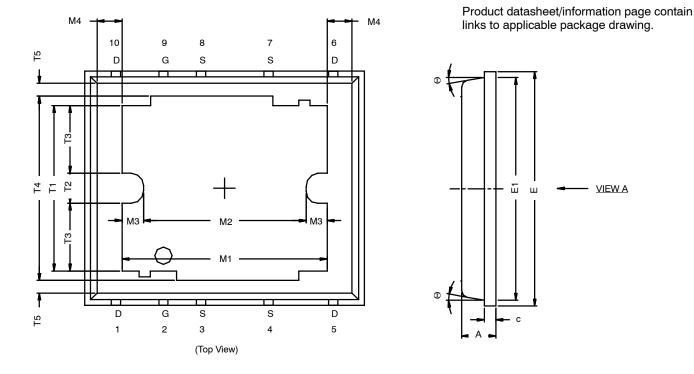
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?74414">www.vishay.com/ppg?74414</a>.

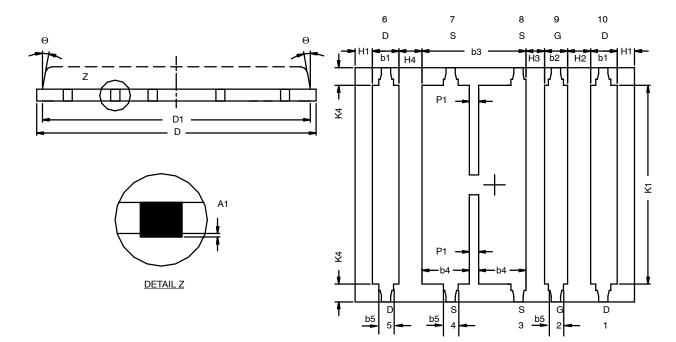
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## Package Information Vishay Siliconix

**PolarPAK**<sup>™</sup> (Option S)





Document Number: 73398 10-Jun-05 <u>VIEW A</u> (Bottom View)

# Vishay Siliconix



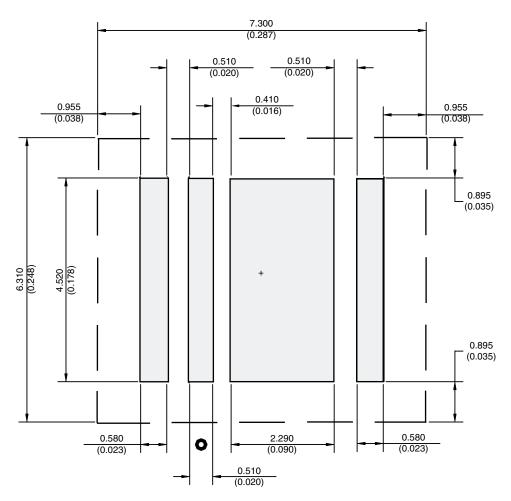
	MI	MILLIMETERS			INCHES	5
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.75	0.80	0.85	0.030	0.031	0.033
A1	0.00	-	0.05	0.000	-	0.002
b1	0.48	0.58	0.68	0.019	0.023	0.027
b2	0.41	0.51	0.61	0.016	0.020	0.024
b3	2.19	2.29	2.39	0.086	0.090	0.094
b4	0.89	1.04	1.19	0.035	0.041	0.047
b5	0.23	0.33	0.43	0.009	0.013	0.017
С	0.20	0.25	0.30	0.008	0.010	0.012
D	6.00	6.15	6.30	0.236	0.242	0.248
D1	5.74	5.89	6.04	0.226	0.232	0.238
Е	5.01	5.16	5.31	0.197	0.203	0.209
E1	4.75	4.90	5.05	0.187	0.193	0.199
H1	0.23	-	-	0.009	-	-
H2	0.45	-	0.56	0.020	-	0.022
H3	0.31	0.41	0.51	0.012	0.016	0.020
H4	0.45	-	0.56	0.020	-	0.022
K1	4.22	4.37	4.52	0.166	0.172	0.178
K4	0.24	-	-	0.009	-	-
M1	4.30	4.50	4.70	0.169	0.177	0.185
M2	3.43	3.58	3.73	0.135	0.141	0.147
M3	0.22	-	-	0.009	-	-
M4	0.05	-	-	0.002	-	-
P1	0.15	0.20	0.25	0.006	0.008	0.010
T1	3.48	3.64	4.10	0.137	0.143	0.150
T2	0.56	0.76	0.95	0.22	0.030	0.037
Т3	1.20	-	-	0.051	-	-
T4	3.90	-	-	0.154	-	-
T5	0	0.18	0.36	0.000	0.007	0.014
Θ	0°	10°	12°	0°	10°	12°

Note: Millimeters govern over inches

Vishay Siliconix



### RECOMMENDED MINIMUM PADS FOR PolarPAK® Option L and S



Recommended Minimum for PolarPAK Option L and S Dimensions in mm/(Inches) No External Traces within Broken Lines Dot indicates Gate Pin (Part Marking)

APPLICATION NOTE

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